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combination of two types of phenomena. Much difficulty in the field of Mott-Anderson metal-
nonmetal transitions arises because these are (1) effects due to electron-electron and electron-
interactions which

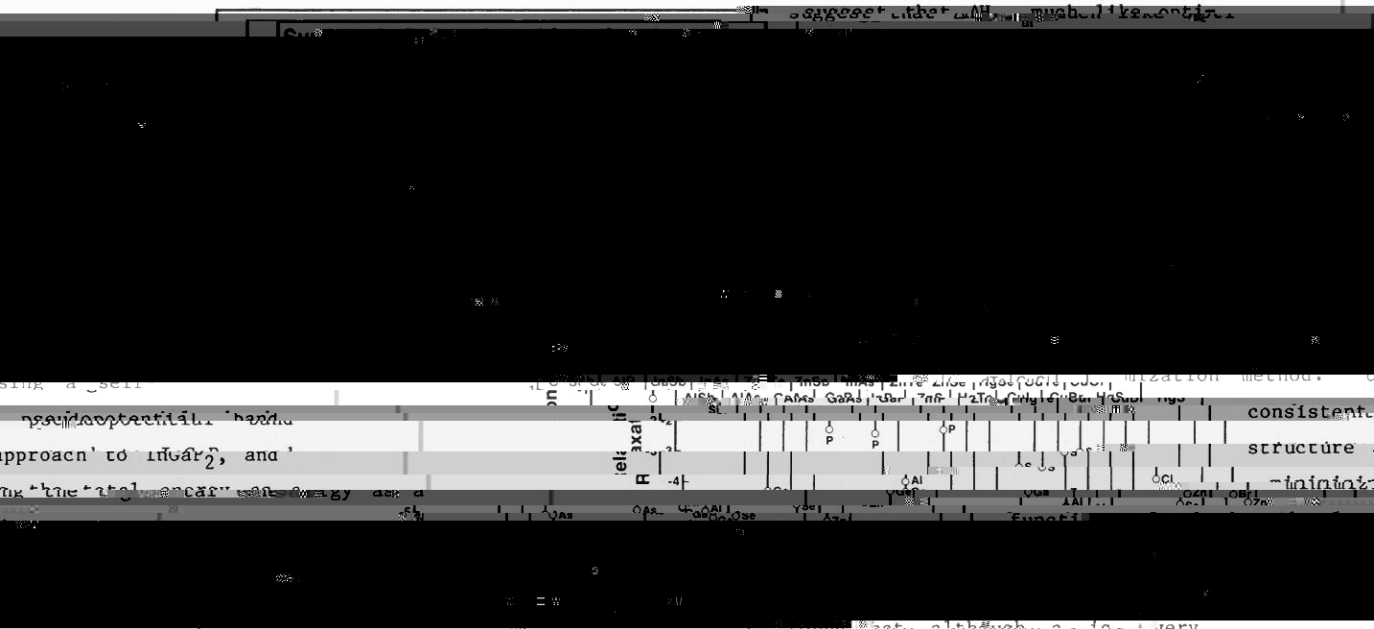

Fig. 1: Calculated bond relaxation (open circles) for isovalent impurities in semiconductors (abscisa). Astriks denote experimental RAKS values.

consistent
structure
found that although a_0 is very close to the average of InP and GaP (Vegards rule), the bond lengths R_{Ga-P} and R_{In-P} are substantially different from